

General Description

The WSP20N10G is the highest performance SGT N-Channel MOSFET with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The WSP20N10G meet the RoHS and Green Product requirement, 100% E_{AS} guaranteed with full function reliability approved.

Features

- 100% UIS Tested.
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

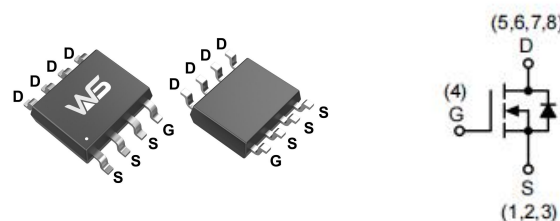
Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D
100V	9.5mΩ	18A

Applications

- Power Management for Industrial DC/DC Converters
- Uninterruptible power supply

SOP-8L Pin Configuration



Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$, Unless Otherwise Noted)

Symbol	Parameter		Rating	Units
V_{DS}	Drain-Source Voltage		100	V
V_{GS}	Gate-Source Voltage		± 20	
I_D ⁷	Continuous Drain Current	$T_C=25^{\circ}\text{C}$	18	A
		$T_C=100^{\circ}\text{C}$	10	
I_{DM} ³	Pulse Drain Current		64	W
P_D ²	Power Dissipation	$T_C=25^{\circ}\text{C}$	3.5	
I_{AS} ³	Single pulse Avalanche Current		19	A
E_{AS} ³	Single pulse Avalanche Energy	$L=0.3\text{mH}$	208	mJ
T_{STG}	Storage Temperature Range		-55 to 150	$^{\circ}\text{C}$
T_J	Operating Junction Temperature Range		-55 to 150	
$R_{\theta JA}$ ^{1,4}	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	21	$^{\circ}\text{C/W}$
		Steady State	65	
$R_{\theta JC}$	Thermal Resistance-Junction to Case		36	

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=15A$	---	9.5	12	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	2.0	2.8	3.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=100V$, $V_{GS}=0V$	---	---	1.0	μA
		$T_J=55^{\circ}\text{C}$	---	---	5.0	
I_{GSS}	Gate-Source Leakage Current	$V_{DS}=0V$, $V_{GS}=\pm 20V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=15A$	---	50	---	S
R_G	Gate Resistance	$f=1.0\text{MHz}$	---	0.7	---	Ω
Q_g	Total Gate Charge (10V)	$V_{DS}=50V$, $V_{GS}=10V$, $I_D=15A$	---	26	---	nC
Q_g	Total Gate Charge (4.5V)		---	15	---	
Q_{gs}	Gate-Source Charge		---	7	---	
Q_{gd}	Gate-Drain Charge		---	7	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=50V$, $V_{GS}=10V$, $I_D=15A$ $R_L=1\Omega$, $R_{GEN}=3\Omega$	---	16	---	ns
T_r	Rise Time		---	9	---	
$T_{d(off)}$	Turn-Off Delay Time		---	35	---	
T_f	Fall Time		---	5	---	
C_{iss}	Input Capacitance	$V_{DS}=50V$, $V_{GS}=0V$, $f=1.0\text{MHz}$	---	1510	---	pF
C_{oss}	Output Capacitance		---	480	---	
C_{rss}	Reverse Transfer Capacitance		---	13	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
I_S ⁷	Continuous Source Current		---	---	18	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=1A$	---	0.7	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=20A$, $di/dt=500A/\mu s$	---	50	---	ns
Q_{rr}	Reverse Recovery Charge		---	100	---	nC

Note:

1. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The Power dissipation P_{DSM} is based on $R_{\theta JA} \leq 10s$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design.
2. The power dissipation P_D is based on $T_{J(MAX)}=150^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
3. Single pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}\text{C}$.
4. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
5. The static characteristics in Figures 1 to 6 are obtained using $<300\mu s$ pulses, duty cycle 0.5% max.
6. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}=150^{\circ}\text{C}$. The SOA curve provides a single pulse rating.
7. The maximum current rating is package limited.
8. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$.
9. The maximum current rating is silicon limited

Typical Characteristics

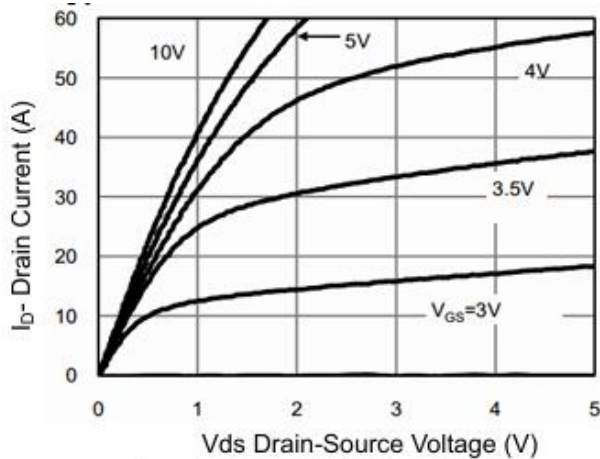


Figure 1 Output Characteristics

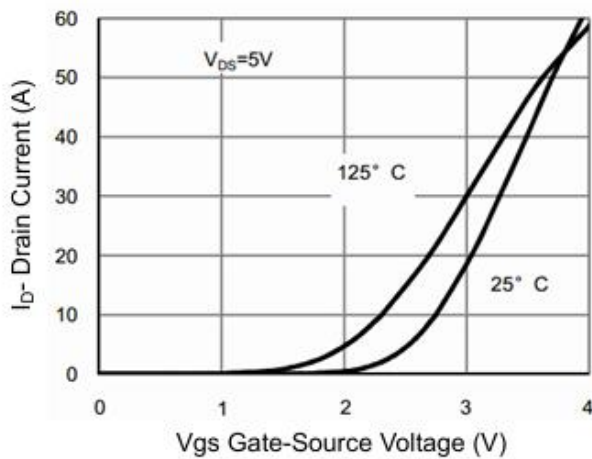


Figure 2 Transfer Characteristics

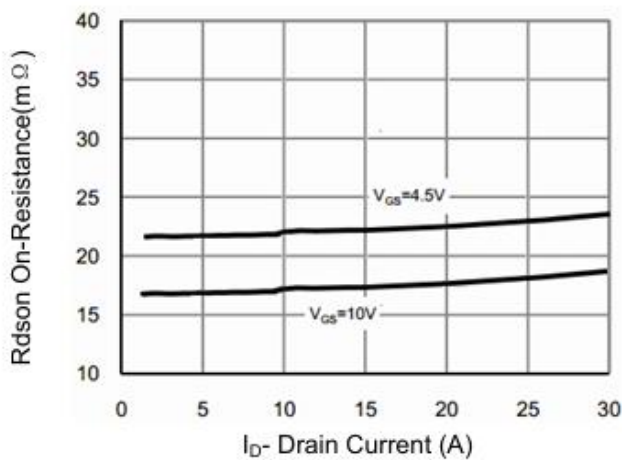


Figure 3 $R_{DS(on)}$ - Drain Current

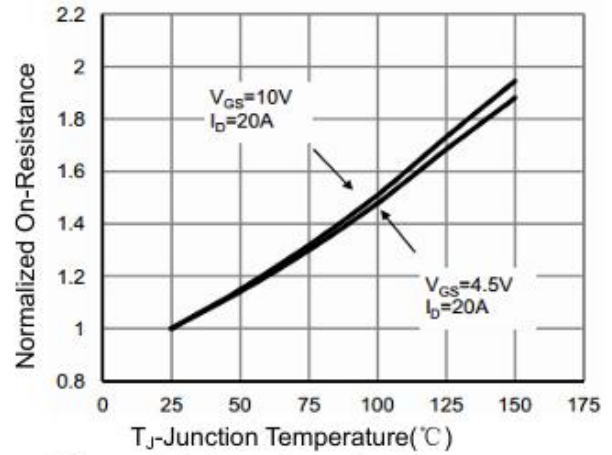


Figure 4 $R_{DS(on)}$ -Junction Temperature

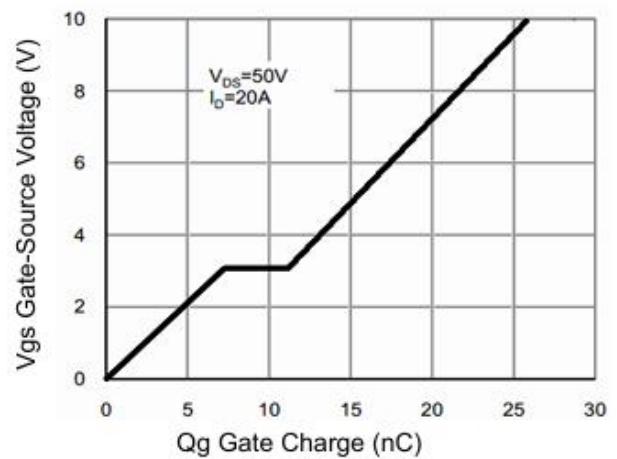


Figure 5 Gate Charge

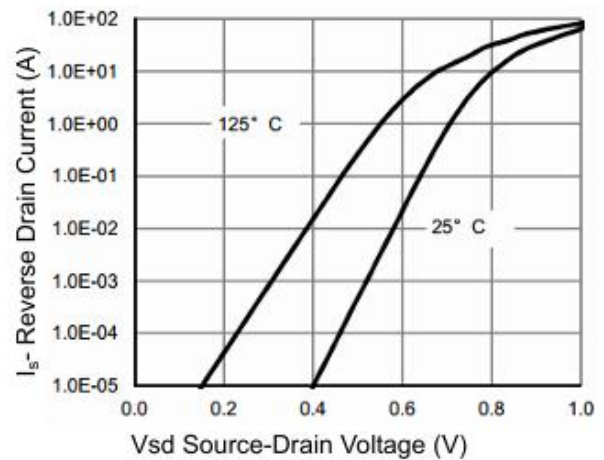


Figure 6 Source- Drain Diode Forward

Typical Characteristics (Cont.)

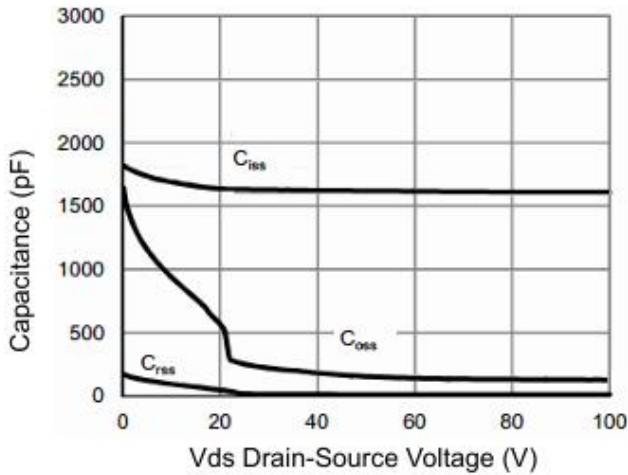


Figure 7 Capacitance vs Vds

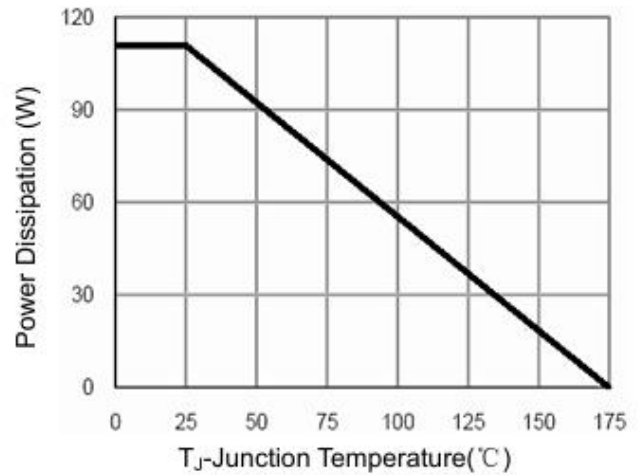


Figure 9 Power De-rating

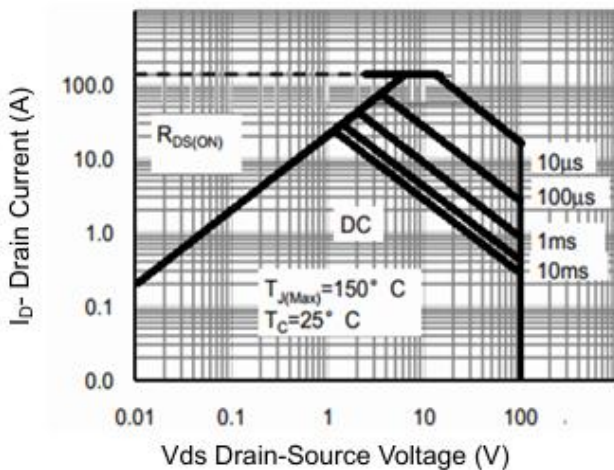


Figure 8 Safe Operation Area

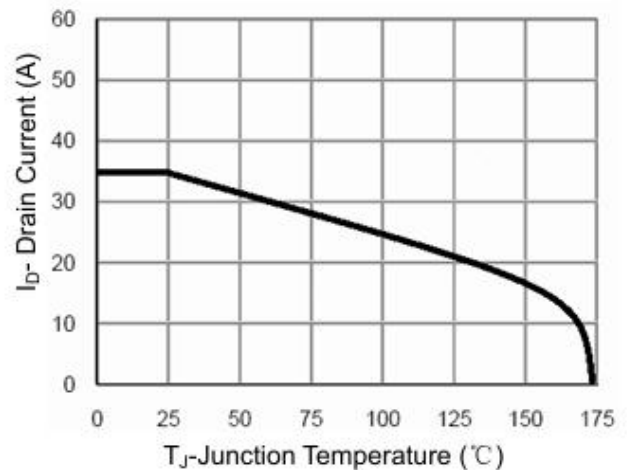


Figure 10 Current De-rating

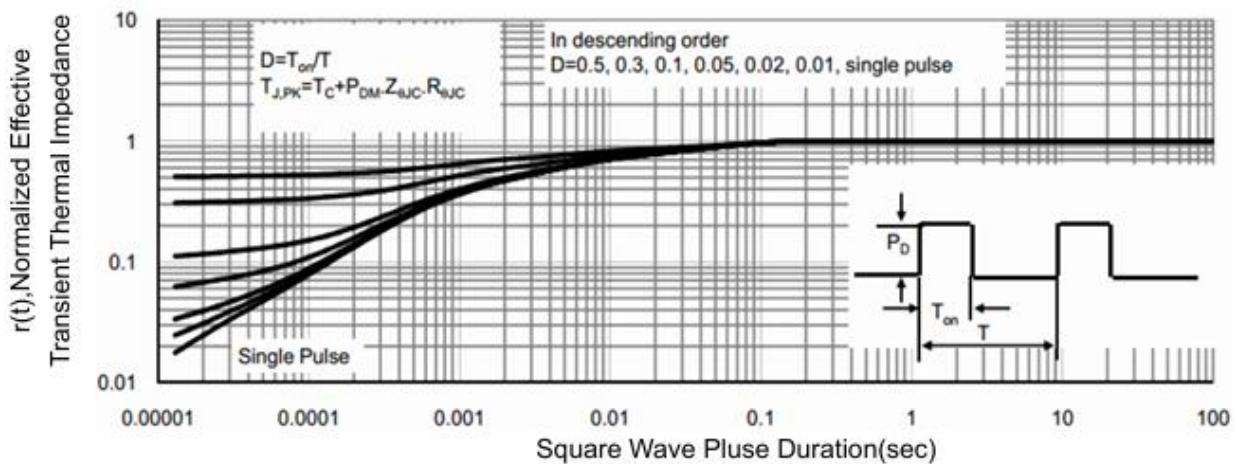
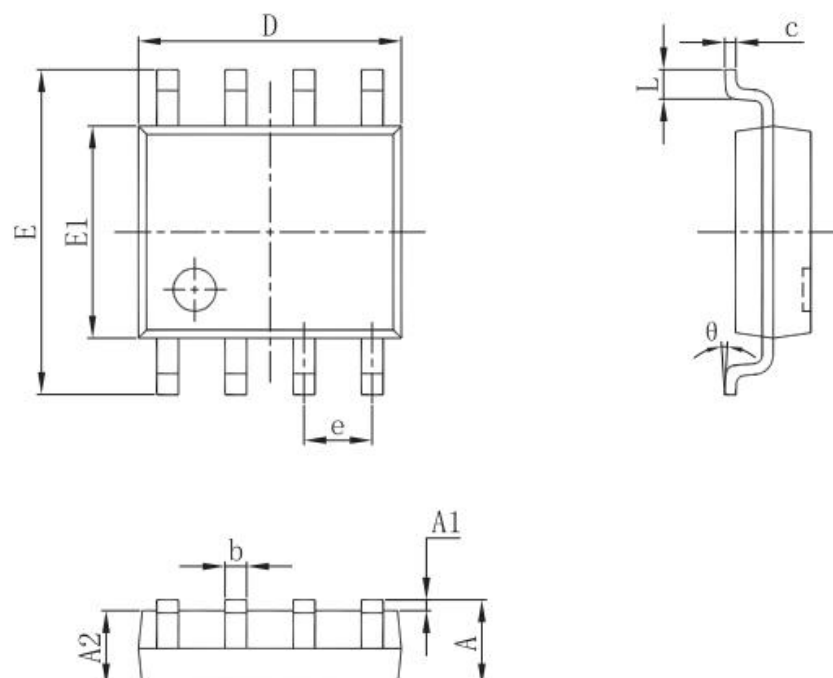


Figure 11 Normalized Maximum Transient Thermal Impedance

Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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